

Amendments to the Claims:

None

Listing of Claims:

Claims 1-14 (canceled)

Claim 15 (withdrawn): A semiconductor device, comprising:

first and second regions in a substrate, the first region being implanted so as to induce stress in the second region; and

an electrical device, at least a portion of the electrical device being formed in the second region.

Claim 16 (withdrawn): The semiconductor device of claim 15, wherein the first region is located beneath at least a portion of the second region.

Claim 17 (withdrawn): The semiconductor device of claim 15, wherein the electrical device comprises at least one of a source/drain region and a channel region formed within the second region.

Claim 18 (withdrawn): The semiconductor device of claim 15, wherein the first region is implanted with at least one of carbon, germanium, and oxygen so as to induce stress in the second region.

Claim 19 (withdrawn): The semiconductor device of claim 18, wherein the first region is implanted with carbon so as to create a tensile stress in the first region.

Claim 20 (withdrawn): The semiconductor device of claim 19, wherein the first region is implanted with one of germanium and oxygen so as to create a compressive stress in the first region.

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Claim 21 (withdrawn): The semiconductor device of claim 20, wherein the implantation of the first region with one of germanium and oxygen induces a compressive stress in the second region.

Claim 22 (withdrawn): The semiconductor device of claim 20, wherein the implantation of the first region with one of germanium and oxygen induces a tensile stress in the second region.

Claims 23-28 (canceled)

Claim 29 (original): A method for forming a MOS transistor, comprising:

providing a semiconductor;

forming a MOS transistor source region in said semiconductor;

forming a MOS transistor drain region in said semiconductor;

forming a MOS channel region in said semiconductor between said source region and said drain region; and

implanting a species in said semiconductor beneath said MOS transistor channel region so as to induce stress in said MOS transistor channel region.

Claim 30 (original): The method of claim 29 wherein said species is selected from a group consisting of oxygen, germanium, and carbon.

Claim 31 (original): The method of claim 29 wherein carbon is implanted beneath said MOS transistor channel region to induce a compressive stress in said MOS transistor channel region.

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Claim 32 (original): A method for forming a MOS transistor, comprising:

providing a semiconductor;

forming a MOS transistor source region in said semiconductor;

forming a MOS transistor drain region in said semiconductor;

forming a MOS channel region in said semiconductor between said source region and said drain region; and

implanting a species in said semiconductor confined to a region substantially beneath said MOS transistor channel region so as to induce stress in said MOS transistor channel region.

Claim 33 (original): The method of claim 32 wherein said species is selected from a group consisting of oxygen, germanium, and carbon.

Claim 34 (original): The method of claim 32 wherein carbon is implanted beneath said MOS transistor channel region to induce a compressive stress in said MOS transistor channel region.

Claim 35 (original): A method for forming a MOS transistor, comprising:

providing a semiconductor;

forming a gate oxide layer on said semiconductor;

forming a MOS transistor gate structure on said gate oxide layer above a first region in said substrate; and

implanting a species in said semiconductor beneath said MOS gate structure so as to induce stress in said first region.

Claim 36 (original): The method of claim 35 wherein said MOS transistor gate structure comprises polysilicon.

Claim 37 (original): The method of claim 36 wherein said species is selected from a group consisting of oxygen, germanium, and carbon.

Claim 38 (original): The method of claim 36 wherein carbon is implanted beneath said MOS transistor gate structure to induce a compressive stress in said MOS transistor channel region.

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